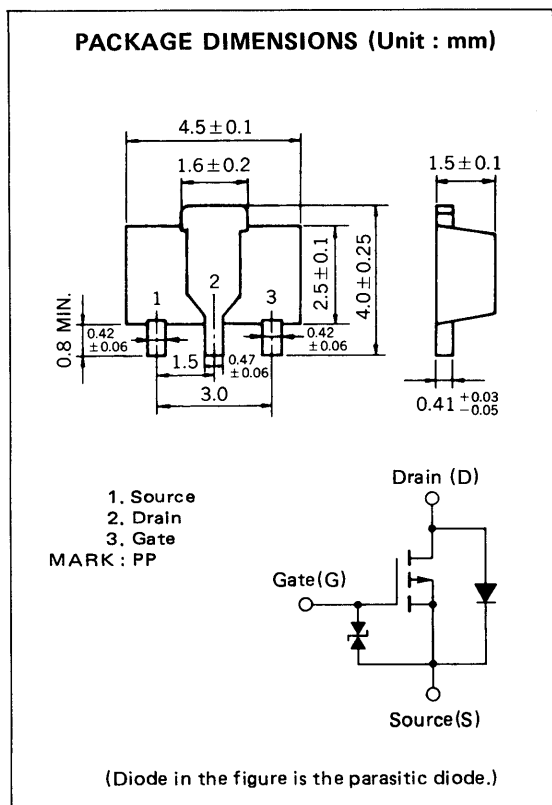


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P1 98.2

P-CHANNEL MOS FET  
FOR SWITCHING



The 2SJ213, P-channel vertical type MOS FET, is a switching device which can be driven directly by the output of ICs having a 5 V power source.

As the MOS FET has low on-state resistance and excellent switching characteristics, it is suitable for driving actuators such as motors, relays, and solenoids.

**FEATURES**

- Directly driven by ICs having a 5 V power supply.
- Has low on-state resistance  
 $R_{DS(on)} = 5.0 \Omega \text{ MAX. @ } V_{GS} = -4.0 \text{ V, } I_D = -0.3 \text{ A}$   
 $R_{DS(on)} = 4.2 \Omega \text{ MAX. @ } V_{GS} = -10 \text{ V, } I_D = -0.3 \text{ A}$

**QUALITY GRADE**

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

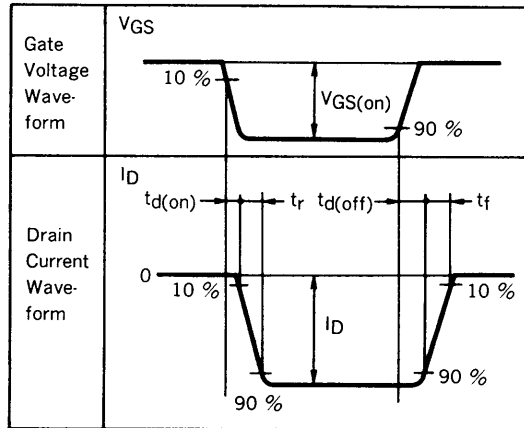
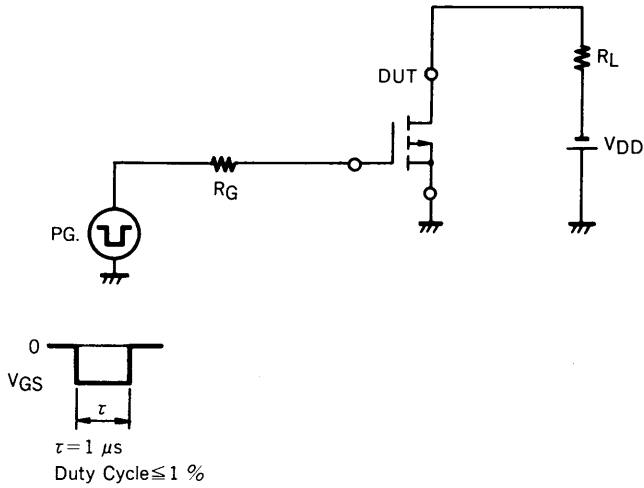
**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

PARAMETER	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	$V_{DSS}$	-100	V	$V_{GS} = 0$
Gate to Source Voltage	$V_{GSS}$	$\pm 20$	V	$V_{DS} = 0$
Drain Current	$I_D(\text{DC})$	$\pm 500$	mA	
Drain Current	$I_D(\text{pulse})$	$\pm 1.0$	A	$PW \leq 10 \text{ ms, Duty Cycle} \leq 50 \%$
Total Power Dissipation	$P_T$	2.0	W	when using ceramic board of $16 \text{ cm}^2 \times 0.7 \text{ mm}$
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$	
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	

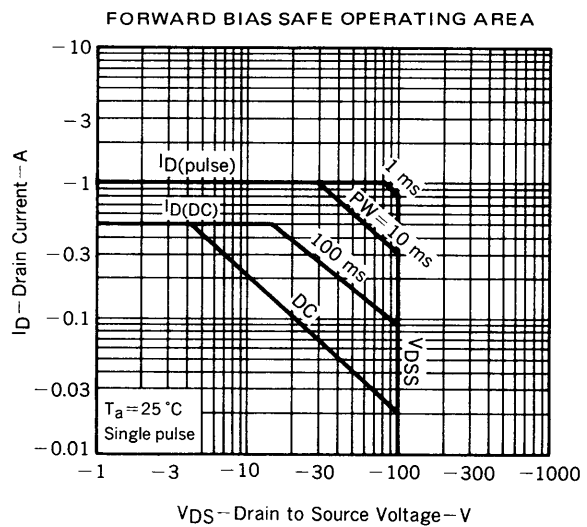
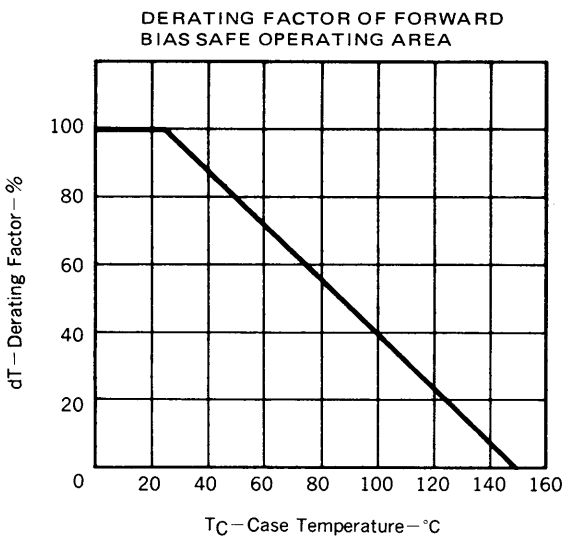
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

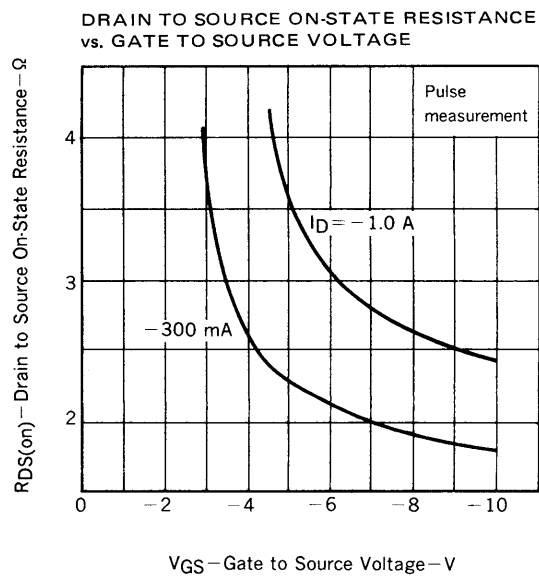
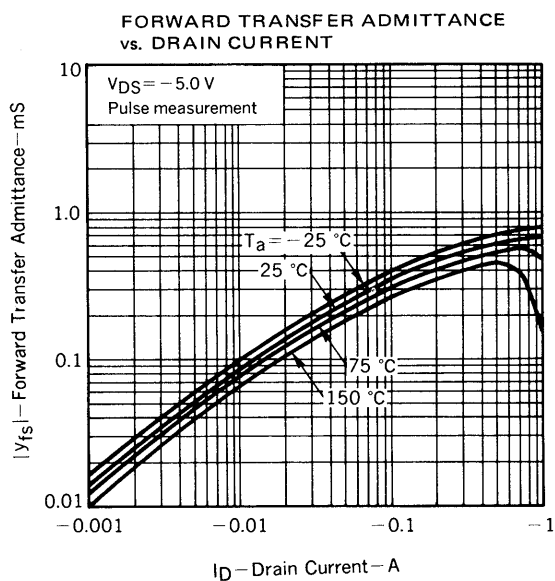
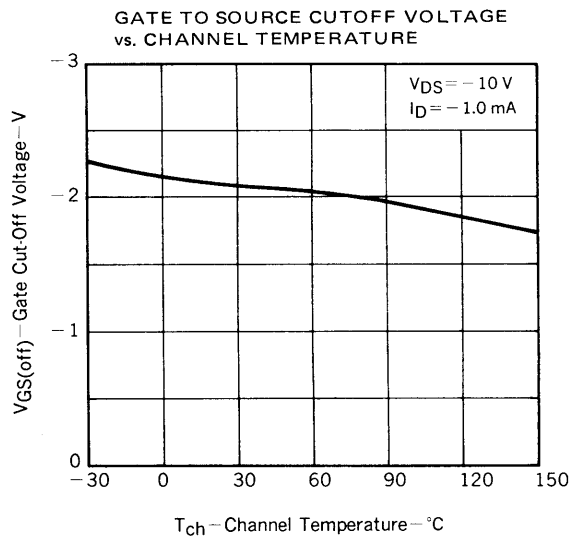
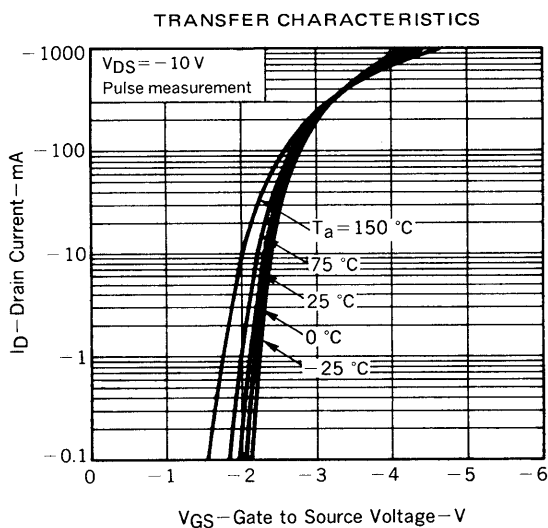
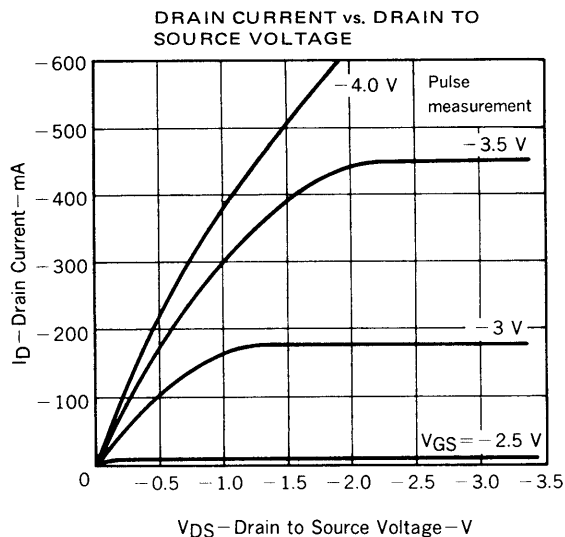
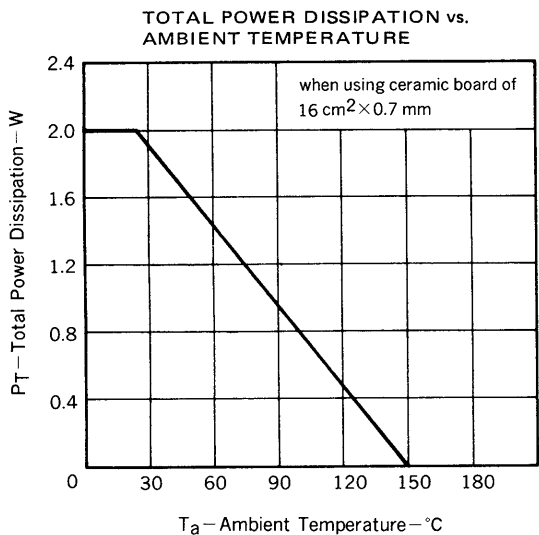
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Breaking Current	$I_{DSS}$			-10	$\mu\text{A}$	$V_{DS} = -100\text{ V}, V_{GS} = 0$
Gate Leakage Current	$I_{GSS}$			$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0$
Gate Cutoff Voltage	$V_{GS(off)}$	-1.0	-2.1	-3.0	V	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $	0.4	0.5		S	$V_{DS} = -5.0\text{ V}, I_D = -300\text{ mA}$
Drain to Source On-State Resistance 1	$R_{DS(on)1}$		2.5	5.0	$\Omega$	$V_{GS} = -4.0\text{ V}, I_D = -300\text{ mA}$
Drain to Source On-State Resistance 2	$R_{DS(on)2}$		1.8	4.2	$\Omega$	$V_{GS} = -10\text{ V}, I_D = -300\text{ mA}$
Input Capacitance	$C_{iss}$		165		pF	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$
Output Capacitance	$C_{oss}$		75		pF	
Feedback Capacitance	$C_{rss}$		13		pF	
On-State Delay Time	$t_{d(on)}$		110		ns	$I_D = -0.3\text{ A}, R_L = 1.5\ \Omega$ $V_{GS(on)} = -4\text{ V}$ $R_G = 10\ \Omega, V_{DD} = -5\text{ V}$
Rise Time	$t_r$		320		ns	
Off-State Delay Time	$t_{d(off)}$		100		ns	
Fall Time	$t_f$		130		ns	

SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS

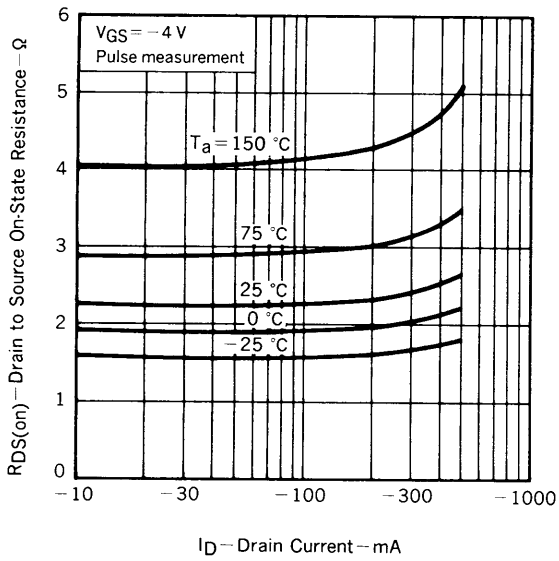


TYPICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

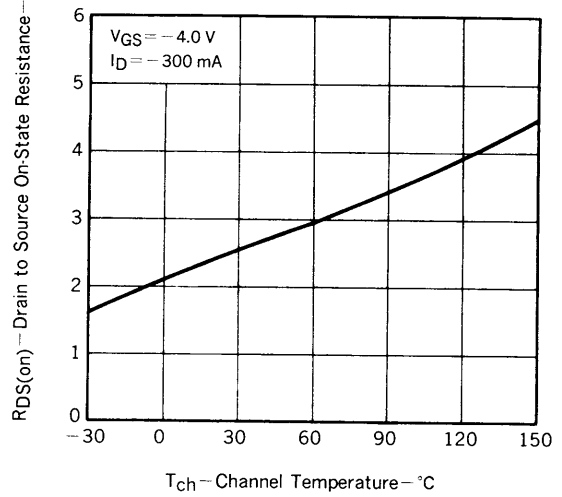




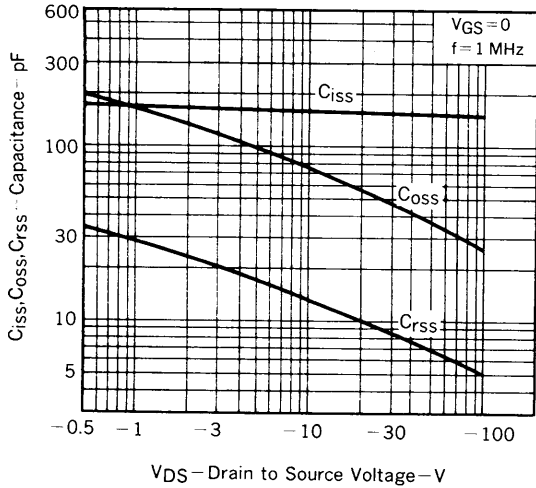
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



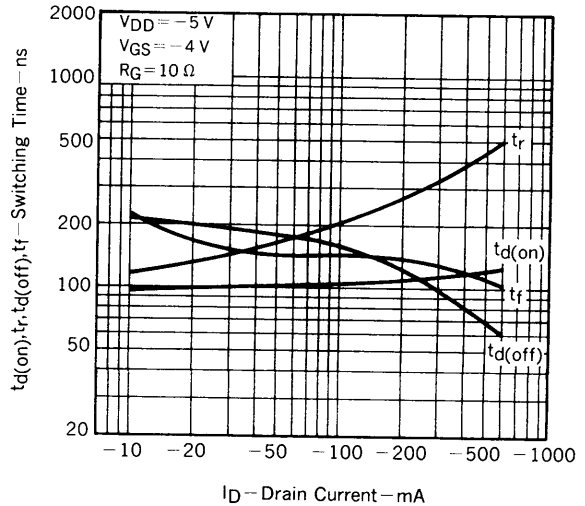
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



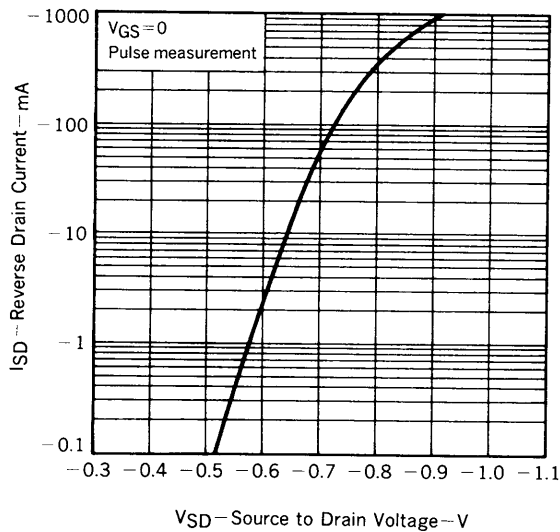
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



**RECOMMENDED SOLDERING CONDITIONS**

Mounting of this product by soldering should be done under the following conditions.  
Please consult our representatives about soldering methods and conditions other than these.

**SURFACE MOUNT TYPE**

For details of the recommended soldering conditions, see the information document.  
"Device Mounting Manual for Surface Mounting (IEI-1207)."

Soldering Method	Soldering Conditions	Symbol for Recommended Conditions
Infrared Reflow	Package peak temp.: 230 °C Soldering time: within 30 sec (above 210 °C) Soldering times: 1, Days limitation: none*	IR30-00
Vapor Phase Soldering	Package peak temp.: 215 °C Soldering time: within 40 sec (above 200 °C) Soldering times: 1, Days limitation: none*	VP15-00
Wave Soldering	Soldering bath temp.: below 260 °C Soldering time: within 10 sec Soldering times: 1, Days limitation: none*	WS60-00

\*: Stored days under storage conditions at 25 °C and below 65 % R.H. after the dry-pack has been opened.

**Note 1:** Combination of soldering methods should be avoided.

**REFERENCE**

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.